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Date Submitted: October 17, 2005

(use as many sheets as necessary)

Complete if Known

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Sheet 1 of 1

Application Number	Unassigned
Filing Date	10/17/2005
First Named Inventor	Tadahiho OHMI
Group Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	039262-0143

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code* (if known)			
T.T.J.	A1	6,399,520	B1	KAWAKAMI et al.	06-04-2002	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document		Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Office ³	Number ⁴	Kind Code* (if known)			
	A2	JP	2002-343961	A	SONY CORP.	11-29-2002	
	A3	JP	2000-294550	A	TOKYO ELECTRON LTD.	10-20-2000	

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ⁶
	A4	M. SATO et al., "Rapid Oxidation of SiC Using Microwave-Discharged O ₂ Plasma at Low Temperatures (<300°C)," Jap. J. of Applied Physics, Part 2, March 1, 2002, Vol. 41:3A, pp. L233-L235.	
	A5	A. GOLZ et al., "Plasma-assisted formation of low defect density SiC-SiO ₂ interfaces," J. of Vacuum Science and Technology B, 1997, Vol. 15:4, pp. 1097-1104.	

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